

<b>FORM 1449*</b> <b>INFORMATION DISCLOSURE STATEMENT</b>  <b>IN AN APPLICATION</b> (Use several sheets if necessary)	Docket Number: 10873.1944USWO	Application Number: <del>Unknown</del> 10/598,095
	Applicant: KITAOKA, et al. 08/17/06	
	Filing Date: <del>Herewith</del>	Group Art Unit: <del>Unknown</del> 1792

U.S. PATENT DOCUMENTS						
EXAMINER INITIAL	DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
/F.H./	2004/183090	September, 2004	Kitaoka, et al.			

FOREIGN PATENT DOCUMENTS							
	DOCUMENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
/F.H./	1-116013	May, 1989	Japan			Abstract	
/F.H./	2000-327495	November, 2000	Japan			Abstract	
/F.H./	2002-293696	October, 2002	Japan			Abstract	
/F.H./	2004-300024	October, 2004	Japan			Abstract	
/F.H./	2005-12171	January, 2005	Japan				

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)		
/F.H./		The Society of Chemical Engineers, Japan, "Kagaku Kogaku Binran", vol. 6, 1999, pgs. 426-427
/F.H./		Kawamura, et al., "Growth of Transparent, Large Size GaN Single Crystal with Low Dislocations using Ca-Na Flux System", Jpn. J. Appl. Phys., Vol. 42

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EXAMINER /Felisa Hiteshew/	DATE CONSIDERED 08/12/2008
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form for next communication to the Applicant.	